

| L. Number | Hits | Search Text | DB | Time stamp |
|-----------|------|--------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------|------------------|
| 1 | 1002 | silazane with silicon\$9 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 09:59 |
| 2 | 2771 | \$20silazane with silicon\$9 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 09:57 |
| 3 | 2563 | (\$20silazane with silicon\$9) and silicon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 09:57 |
| 4 | 391 | ((\$20silazane with silicon\$9) and silicon) and dielectric | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 09:57 |
| 5 | 314 | (((\$20silazane with silicon\$9) and silicon) and dielectric) and substrate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 09:58 |
| 6 | 262 | ((((\$20silazane with silicon\$9) and silicon) and dielectric) and substrate) and (conduct\$3 polysilicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 13:45 |
| 7 | 70 | (((((\$20silazane with silicon\$9) and silicon) and dielectric) and substrate) and (conduct\$3 polysilicon)) and (\$20silazane with deposit\$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 13:46 |
| 9 | 3 | "10273667" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 10:11 |
| 10 | 29 | ((((((\$20silazane with silicon\$9) and silicon) and dielectric) and substrate) and (conduct\$3 polysilicon)) and (\$20silazane with dielectric) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 13:46 |
| - | 240 | dielectric adj (layer film) with (silicon adj containing) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/20 15:27 |
| - | 57 | (dielectric adj (layer film) with (silicon adj containing)) and ((silicon react\$3 gas\$2) near\$3 source\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/20 15:53 |
| - | 57 | ((dielectric adj (layer film) with (silicon adj containing)) and ((silicon react\$3 gas\$2) near\$3 source\$1)) and (conduct\$3 near\$3 (layer film)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 08:48 |

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| 302 | ((silicon adj containing) with (dielectric near3 (layer film))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 08:51 |
| 148 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (source gas\$2)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 08:53 |
| 3 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (source gas\$2)) and silazane | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 09:30 |
| 3 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with silazane) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 09:33 |
| 0 | (silicon adj containing) with (silicon with silazane) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/19 09:48 |
| 63 | (silicon adj containing) with (silicon with silazane) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 08:57 |
| 4 | ((silicon adj containing) with (silicon with silazane)) and nitridi\$4 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 08:57 |
| 1 | "6197628".PN | USPAT | 2002/09/23 08:58 |
| 1 | "5637527".PN | USPAT | 2002/09/23 08:59 |
| 708 | (silicon with silazane) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 09:08 |
| 18 | dielectric with (silicon with nitridizing) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 09:03 |
| 116 | semiconductor and (silicon with silazane) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 09:33 |
| 63 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (silazane silane)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 09:34 |
| 9 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (silazane silane)) and (nitridation nitridization nitridizing) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/23 09:35 |

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|---|-----|--------------------------------------------------------------------------------------------------------------------------------------------|-----------|------------------|
| - | 13 | dielectric with (silicon with silazane) | USPAT; | 2003/02/11 09:28 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| - | 605 | (silicon adj containing) with dielectric | IBM_TDB | |
| | | | USPAT; | 2003/02/11 09:29 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| - | 204 | ((silicon adj containing) with dielectric) and (conduct\$3 adj (layer film)) | IBM_TDB | |
| | | | USPAT; | 2003/02/11 09:33 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| - | 69 | ((silicon adj containing) with dielectric) and (conduct\$3 adj (layer film))) and ((silicon adj containing) with (react\$4 agent ambient)) | IBM_TDB | |
| | | | USPAT; | 2003/02/11 12:47 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| - | 1 | "6358838".PN. | IBM_TDB | |
| - | 1 | "5461010".PN. | USPAT | 2003/02/11 09:47 |
| - | 1 | "6214748".PN. | USPAT | 2003/02/11 09:52 |
| - | 1 | ("5567661").PN. | USPAT | 2003/02/11 09:52 |
| - | 1 | "5320875".PN. | USPAT | 2003/02/11 12:47 |
| - | 1 | "5318928".PN. | USPAT | 2003/02/11 14:04 |
| - | 1 | "5298587".PN. | USPAT | 2003/02/11 14:04 |
| - | 1 | "5000113".PN. | USPAT | 2003/02/11 14:05 |
| | | | USPAT | 2003/02/11 14:05 |

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|-----------|------|-----------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------|------------------|
| - | 240 | dielectric adj (layer film) with (silicon adj containing) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/20 15:27 |
| - | 57 | ((dielectric adj (layer film) with (silicon adj containing)) and ((silicon react\$3 gas\$2) near3 source\$1)) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/20 15:53 |
| - | 57 | ((dielectric adj (layer film) with (silicon adj containing)) and ((silicon react\$3 gas\$2) near3 source\$1)) and (conduct\$3 near\$3 (layer film)) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/23 08:48 |
| - | 302 | (silicon adj containing) with (dielectric near3 (layer film)) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/23 08:51 |
| - | 148 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (source gas\$2)) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/23 08:53 |
| - | 3 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (source gas\$2)) and silazane | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2003/02/11 09:30 |
| - | 3 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with silazane) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/23 09:33 |
| - | 0 | (silicon adj containing) with (silicon with silazane) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/23 08:56 |
| - | 63 | (silicon adj containing) with (silicon with silazane) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/23 08:57 |
| - | 4 | ((silicon adj containing) with (silicon with silazane)) and nitridi\$4 | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/23 08:57 |
| - | 1 | "6197628".PN. | USPAT | 2002/09/23 08:58 |
| - | 1 | "5637527".PN. | USPAT | 2002/09/23 08:59 |
| - | 708 | (silicon with silazane) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/23 09:08 |
| - | 18 | dielectric with (silicon with nitridizing) | USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB | 2002/09/23 09:03 |

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|---|-----|--------------------------------------------------------------------------------------------------------------------------------------------------|-----------|------------------|
| - | 116 | semiconductor and (silicon with silazane) | USPAT; | 2002/09/23 09:33 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 63 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (silazane silane)) | USPAT; | 2002/09/23 09:34 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 9 | ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (silazane silane)) and (nitridation nitridization nitridizing) | USPAT; | 2002/09/23 09:35 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 13 | dielectric with (silicon with silazane) | USPAT; | 2003/02/11 09:28 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 605 | (silicon adj containing) with dielectric | USPAT; | 2003/02/11 09:29 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 204 | ((silicon adj containing) with dielectric) and (conduct\$3 adj (layer film)) | USPAT; | 2003/02/11 09:33 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 69 | ((silicon adj containing) with dielectric) and (conduct\$3 adj (layer film)) and ((silicon adj containing) with (react\$4 agent ambient)) | USPAT; | 2003/02/11 12:47 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 1 | "6358838".PN. | USPAT | 2003/02/11 09:47 |
| - | 1 | "5461010".PN. | USPAT | 2003/02/11 09:52 |
| - | 1 | "6214748".PN. | USPAT | 2003/02/11 09:52 |
| - | 1 | ("5567661").PN. | USPAT | 2003/02/11 12:47 |
| - | 1 | "5320875".PN. | USPAT | 2003/02/11 14:04 |
| - | 1 | "5318928".PN. | USPAT | 2003/02/11 14:04 |
| - | 1 | "5298587".PN. | USPAT | 2003/02/11 14:05 |
| - | 1 | "5000113".PN. | USPAT | 2003/02/11 14:05 |

U.S. Patent Dec. 22, 1996 Sheet 1 of 4 5,567,661

FIG. 1A

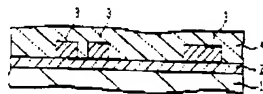
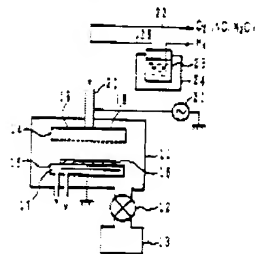


FIG. 1B



example, organic silicon materials having the structures shown in FIGS. 2A to 2D may be used. It is preferable to use silazane compound having a ring or cyclosilazane structure.

(53) O.sub.2, N.sub.2O, and NO may be used as oxidant, and other oxidants may also be used. NF.sub.3 or NH.sub.3 may be added to the oxidant. It is apparent to those skilled in the art that various modifications, improvements, combinations and the like can be made without departing from the scope of the appended claims.

CLAIMS:

We claim:

1. A method of manufacturing a semiconductor device having an insulating film comprising the steps of:

preparing a semiconductor substrate having one of convexities and concavities which create a step height on a surface thereof; and

generating plasma by using organic silicon having tri- or more silazane bonding and oxidant and depositing a planarized insulating film on said semiconductor substrate by plasma chemical vapor deposition at a substrate temperature of about 100.degree. C. or lower in order to significantly reduce

| | U | 1 | Document ID | Issue Date | Pages | Title |
|----|--------------------------|--------------------------|--------------|------------|-------|--------------------------------|
| 21 | <input type="checkbox"/> | <input type="checkbox"/> | US 5567661 A | 19961022 | 12 | Formation of planarized insula |
| 22 | <input type="checkbox"/> | <input type="checkbox"/> | US 5508368 A | 19960416 | 15 | Ion beam process for deposit |

S. Patent

Apr. 30, 2002

Sheet 2 of 3

US 6,380

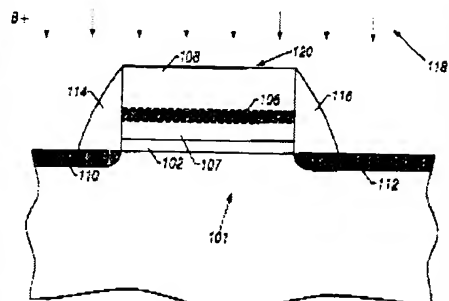


FIG. 1C

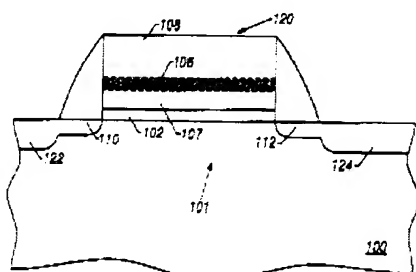


FIG. 1D

small amount of the dopant is preferably implanted into the region of the barrier region 106 or into the polysilicon region 107 layer below the barrier region 106. Through subsequent heat treatment operations (e.g., implant anneal steps) the barrier region 106 retards the downward diffusion of the boron and helps prevent boron from reaching the gate dielectric 102/polysilicon 104 interface. Alternatively, the dopant profile may exist entirely within the upper layer of polysilicon 108. In either case, the barrier region 106 retards the downward diffusion of dopant toward the gate dielectric 102 and toward the channel region 101.

In another embodiment generally following the sequence depicted in FIGS 1A-1D, the barrier region 106 may be formed by depositing a nitrogen-containing layer, such as silicon nitride or titanium nitride, onto the top surface of polysilicon 104. Suitable conditions for depositing a layer of silicon nitride are low pressure chemical vapor deposition (LPCVD), plasma deposition and deposition by sputtering. Suitable conditions for depositing a layer of titanium nitride are low pressure chemical vapor deposition, plasma deposition and deposition by sputtering. Such a layer of titanium nitride is electrically conductive and thus helps ensure a good electrical connection between polysilicon region 107 and polysilicon region 108.

FIG. 3 is a cross-sectional view of a multi-layer structure incorporating three polysilicon layers, with a separate barrier region between each adjacent

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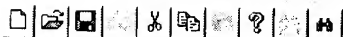
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- 🔍 (57) (dielectric adj (layer film) with (silicon adj containing)) and ((silicon react\$3 gas\$2)..
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- 🔍 (302) (silicon adj containing) with (dielectric near3 (layer film))
- 🔍 (148) ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (sour..
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- 🔍 (0) (silicon adj containing) with (silicon with silazane)
- 🔍 (63) (silicon adj containing) with (silicon with silazane)
- 🔍 (4) ((silicon adj containing) with (silicon with silazane)) and nitridi\$4
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- 🔍 (1) "5637527".PN.
- 🔍 (708) (silicon with silazane)
- 🔍 (7) dielectric with (silicon with silazane)
- 🔍 (18) dielectric with (silicon with nitridizing)
- 🔍 (116) semiconductor and (silicon with silazane)
- 🔍 (63) ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (silaz...
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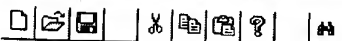
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- ☞ (302) (silicon adj containing) with (dielectric near3 (layer film))
- ☞ (148) ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (sour...
- ☞ (3) (((silicon adj containing) with (dielectric near3 (layer film)))) and (silicon with (sourc...
- ☞ (3) (((silicon adj containing) with (dielectric near3 (layer film)))) and (silicon with silazane)
- ☞ (0) (silicon adj containing) with (silicon with silazane)
- ☞ (63) (silicon adj containing) with (silicon with silazane)
- ☞ (4) ((silicon adj containing) with (silicon with silazane)) and nitridi\$4
- ☞ (1) "6197628".PN.
- ☞ (1) "5637527".PN.
- ☞ (708) (silicon with silazane)
- ☞ (18) dielectric with (silicon with nitridizing)
- ☞ (116) semiconductor and (silicon with silazane)
- ☞ (63) ((silicon adj containing) with (dielectric near3 (layer film))) and (silicon with (silaz...
- ☞ (9) (((silicon adj containing) with (dielectric near3 (layer film)))) and (silicon with (silaz...

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dielectric with
(silicon with
silazane)

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|---|--------------------------|--------------------------|----------------------|------------|-------|------------------------------------------|------------|--------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030008989 A1 | 20030109 | 12 | Polymer synthesis and films therefrom | 526/227 | 526/219; |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030006477 A1 | 20030109 | 17 | Porous materials | 257/527 | 526/303.1; |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030004218 A1 | 20030102 | 18 | Porous materials | 521/77 | |

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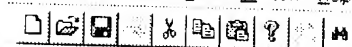


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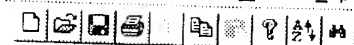
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☒ L10: (29) 6 and (\$20silazane with dielectric)

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|----|-------------------------------------|--------------------------|---------------|------------|-------|--------------------------------------------------------------------------------|------------|--------------|
| 17 | <input type="checkbox"/> | <input type="checkbox"/> | US 6426127 B1 | 20020730 | 12 | Electron beam modification of perhydrosilazane spin-on glass | 427/503 | 427/496; |
| 18 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6383466 B1 | 20020507 | 11 | Method of dehydroxylating a hydroxylated material and method of | 423/335 | 427/497; |
| 19 | <input type="checkbox"/> | <input type="checkbox"/> | US 6245690 B1 | 20010612 | 22 | Method of improving moisture | 438/780 | 516/100; |
| 20 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6074939 A | 20000613 | 14 | Method for fabricating semiconductor device | 438/596 | 516/111 |
| 21 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6066573 A | 20000523 | 5 | Method of producing dielectric film | 438/778 | 257/E21.263; |
| 22 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6061112 A | 20000509 | 13 | Method of fabricating a reflection type liquid crystal display in which th | 349/113 | 257/E21.277; |
| 23 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6007878 A | 19991228 | 25 | Process for producing an optical recording medium having a protective | 427/562 | 257/E21.703; |
| 24 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5940154 A | 19990817 | 12 | Reflection type liquid crystal display and method of fabricating the same | 349/113 | 257/E27.112; |
| 25 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5393815 A | 19950228 | 7 | Silazane-based, heat resistant, dielectric coating compositions | 524/262 | 257/632; |
| 26 | <input type="checkbox"/> | <input type="checkbox"/> | US 5318928 A | 19940607 | 4 | Method for the surface passivation of sensors using an in situ sputter clean | 438/50 | 257/758; |
| 27 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5254411 A | 19931019 | 9 | Formation of heat-resistant dielectric coatings | 428/447 | 349/158 |
| 28 | <input type="checkbox"/> | <input type="checkbox"/> | US 4719125 A | 19880112 | 6 | Cyclosilazane polymers as dielectric films in integrated circuit fabrication t | 438/780 | 427/563; |
| 29 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | DE 3490007 T | 19840605 | | Semiconductor device mfr. using poly:silazane coating - patterned then | | 427/564; |


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☒ L10: (29) 6 and (\$20silazane with dielectric)

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| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030030082 A1 | 20030213 | 8 | Method of forming an ultra thin dielectric film and a semiconductor d | 257/288 | 257/324; |
| 6 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20020182849 A1 | 20021205 | 5 | METHOD FOR FABRICATING A LOW DIELECTRIC CONSTANT | 438/623 | 257/411; |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020182845 A1 | 20021205 | 17 | Method of filling a concave portion with an insulating material | 438/618 | 438/197 |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020172898 A1 | 20021121 | 9 | Layered hard mask and dielectric materials and methods therefor | 430/328 | 427/596; |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020160614 A1 | 20021031 | 16 | Method of forming an interlayer dielectric film | 438/694 | 430/311; |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020135031 A1 | 20020926 | 15 | Method for forming a dielectric layer and semiconductor device incorporati | 257/405 | |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020064936 A1 | 20020530 | 6 | Method of forming interlevel dielectric layer of semiconductor devi | 438/623 | 438/626; |
| 12 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020043695 A1 | 20020418 | 9 | Method for forming an ultra thin dielectric film and a semiconductor d | 257/435 | 438/631 |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010026849 A1 | 20011004 | 23 | Method of improving moisture resistance of low dielectric constant fi | 427/569 | 118/723R; |
| 14 | <input type="checkbox"/> | <input type="checkbox"/> | US 6479399 B2 | 20021112 | 6 | Method of forming interlevel dielectric layer of semiconductor devi | 438/738 | 427/376.2; |
| 15 | <input type="checkbox"/> | <input type="checkbox"/> | US 6448187 B2 | 20020910 | 22 | Method of improving moisture resistance of low dielectric constant fi | 438/758 | 438/624; |
| 16 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6433359 B1 | 20020813 | 11 | Surface modifying layers for organic thin film transistors | 257/40 | 257/E21.263; |
| 17 | <input type="checkbox"/> | <input type="checkbox"/> | US 6426127 B1 | 20020730 | 12 | Electron beam modification of perhydrosilazane spin-on glass | 427/503 | 257/E21.277; |
| 18 | <input type="checkbox"/> | <input type="checkbox"/> | US 6382166 B1 | 20020507 | 11 | Method of dehydrocondensation | 427/325 | 438/99 |

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L9: (3) "10273667"

L10: (29) 6 and (\$20silazane with dielectric)

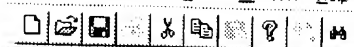
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| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030062599 A1 | 20030403 | 19 | Process for producing semiconductor substrates and semico | 257/632 | 257/635; |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030054667 A1 | 20030320 | 24 | Method of improving moisture resistance of low dielectric constant fi | 438/780 | 257/642; 438/623; |
| 3 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20030054616 A1 | 20030320 | 27 | Electronic devices and methods of manufacture | 438/400 | 438/638 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030052338 A1 | 20030320 | 14 | Dielectric layer for semiconductor device having less current leakage and | 257/200 | |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030030082 A1 | 20030213 | 8 | Method of forming an ultra thin dielectric film and a semiconductor d | 257/288 | 257/324; 257/411; |
| 6 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20020182849 A1 | 20021205 | 5 | METHOD FOR FABRICATING A LOW DIELECTRIC CONSTANT | 438/623 | |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020182845 A1 | 20021205 | 17 | Method of filling a concave portion with an insulating material | 438/618 | 438/197 |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020172898 A1 | 20021121 | 9 | Layered hard mask and dielectric materials and methods therefor | 430/328 | 427/596; 430/311; |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020160614 A1 | 20021031 | 16 | Method of forming an interlayer dielectric film | 438/694 | |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020135031 A1 | 20020926 | 15 | Method for forming a dielectric layer and semiconductor device incorporati | 257/405 | |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020064936 A1 | 20020530 | 6 | Method of forming interlevel dielectric layer of semiconductor devi | 438/623 | 438/626; 438/631 |
| 12 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020043695 A1 | 20020418 | 9 | Method for forming an ultra thin dielectric film and a semiconductor d | 257/435 | |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010026849 A1 | 20011004 | 23 | Method of improving moisture resistance of low dielectric constant fi | 427/569 | 118/723R; 427/376.2; |
| 14 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010026849 A1 | 20011004 | 23 | Method of forming interlevel | 427/569 | 427/376.2; |

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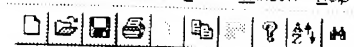

☒ L7: (70) 6 and (\$20silazane with deposit\$3)

☒ L10: (29) 6 and (\$20silazane with dielectric)

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| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030062599 A1 | 20030403 | 19 | Process for producing semiconductor substrates and semico | 257/632 | 257/635; |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030060302 A1 | 20030327 | 15 | Highly durable and abrasion resistant composite diamond-like carbon deco | 473/282 | 257/642; |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030054667 A1 | 20030320 | 24 | Method of improving moisture resistance of low dielectric constant fi | 438/780 | 438/623; |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030052338 A1 | 20030320 | 14 | Dielectric layer for semiconductor device having less current leakage and | 257/200 | 438/638 |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030030082 A1 | 20030213 | 8 | Method of forming an ultra thin dielectric film and a semiconductor d | 257/288 | 257/324; |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030017623 A1 | 20030123 | 13 | Reliable adhesion layer interface structure for polymer memory electro | 438/3 | 257/411; |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020182845 A1 | 20021205 | 17 | Method of filling a concave portion with an insulating material | 438/618 | 438/197 |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020172898 A1 | 20021121 | 9 | Layered hard mask and dielectric materials and methods therefor | 430/328 | 427/596; |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020160614 A1 | 20021031 | 16 | Method of forming an interlayer dielectric film | 438/694 | 430/311; |
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| 12 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020064936 A1 | 20020530 | 6 | Method of forming interlevel dielectric layer of semiconductor devi | 438/623 | 438/626; |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020060348 A1 | 20020523 | 9 | System and device including a barrier layer | 257/412 | 438/631 |

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☒ L7: (70) 6 and (\$20silazane with deposit\$3)

☒ L10: (29) 6 and (\$20silazane with dielectric)

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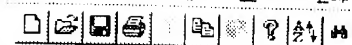
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| 16 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020032073 A1 | 20020314 | 15 | HIGHLY DURABLE AND ABRASION RESISTANT COMPO | 473/324 | 473/349 |
| 17 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020025658 A1 | 20020228 | 9 | Method for forming a barrier layer | 438/486 | |
| 18 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020015135 A1 | 20020207 | 32 | Image projection system with a polarizing beam splitter | 353/31 | |
| 19 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010034076 A1 | 20011025 | 16 | Process for wafer level treatment to reduce stiction and passivate microm | 438/50 | 438/780 |
| 20 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010029114 A1 | 20011011 | 6 | Method of forming polymeric layers of silicon oxynitride | 438/794 | 438/790 |
| 21 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010026849 A1 | 20011004 | 23 | Method of improving moisture resistance of low dielectric constant fi | 427/569 | 118/723R; |
| 22 | <input type="checkbox"/> | <input type="checkbox"/> | US 6501014 B1 | 20021231 | 15 | Coated article and solar battery module | 136/256 | 427/376.2; |
| 23 | <input type="checkbox"/> | <input type="checkbox"/> | US 6479399 B2 | 20021112 | 6 | Method of forming interlevel dielectric layer of semiconductor devi | 438/738 | 136/251; |
| 24 | <input type="checkbox"/> | <input type="checkbox"/> | US 6475883 B2 | 20021105 | 9 | Method for forming a barrier layer | 438/486 | 257/434; |
| 25 | <input type="checkbox"/> | <input type="checkbox"/> | US 6448187 B2 | 20020910 | 22 | Method of improving moisture resistance of low dielectric constant fi | 438/758 | 438/623; |
| 26 | <input type="checkbox"/> | <input type="checkbox"/> | US 6447120 B2 | 20020910 | 33 | Image projection system with a polarizing beam splitter | 353/20 | 438/624; |
| 27 | <input type="checkbox"/> | <input type="checkbox"/> | US 6426127 B1 | 20020720 | 13 | Electron beam modification of | 438/486 | 438/398; |

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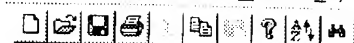

☒ L7: (70) 6 and (\$20silazane with deposit\$3)

☒ L10: (29) 6 and (\$20silazane with dielectric)

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| 28 | <input type="checkbox"/> | <input type="checkbox"/> | US 6410968 B1 | 20020625 | 8 | perhydrosilazane spin-on glass | 257/412 | 427/497; |
| 29 | <input type="checkbox"/> | <input type="checkbox"/> | US 6379988 B1 | 20020430 | 24 | Semiconductor device with barrier | 438/51 | 438/287 |
| 30 | <input type="checkbox"/> | <input type="checkbox"/> | US 6335224 B1 | 20020101 | 11 | layer | 438/114 | 438/106; |
| 31 | <input type="checkbox"/> | <input type="checkbox"/> | US 6245690 B1 | 20010612 | 22 | Pre-release plastic packaging of | 438/780 | 438/115; |
| 32 | <input type="checkbox"/> | <input type="checkbox"/> | US 5976466 A | 19991102 | 34 | MEMS and IMEMS devices | 422/82.11 | 438/113; |
| 33 | <input type="checkbox"/> | <input type="checkbox"/> | US 5776603 A | 19980707 | 8 | Protection of microelectronic devices | 428/336 | 438/460; |
| 34 | <input type="checkbox"/> | <input type="checkbox"/> | US 5733611 A | 19980331 | 14 | during packaging | 427/591 | 257/E21.263; |
| 35 | <input type="checkbox"/> | <input type="checkbox"/> | US 5679413 A | 19971021 | 15 | Method of improving moisture | 427/534 | 257/E21.277; |
| 36 | <input type="checkbox"/> | <input type="checkbox"/> | US 5618619 A | 19970408 | 14 | resistance of low dielectric constant fi | 428/334 | 250/361C; |
| 37 | <input type="checkbox"/> | <input type="checkbox"/> | US 5380553 A | 19950110 | 14 | Multiple-probe diagnostic sensor | 427/534 | 250/461.1; |
| 38 | <input type="checkbox"/> | <input type="checkbox"/> | US 5322913 A | 19940621 | 30 | Glazing pane equipped with at least | 427/527; | 359/580; |
| 39 | <input type="checkbox"/> | <input type="checkbox"/> | US 5318928 A | 19940607 | 4 | one thin film and method of manufact | 427/527; | 359/586; |
| 40 | <input type="checkbox"/> | <input type="checkbox"/> | US 5318927 A | 19940607 | 4 | Method for densification of porous | 427/534; | 427/255.6; |
| | <input type="checkbox"/> | <input type="checkbox"/> | US 5318926 A | 19940607 | 4 | billets | 427/527; | 427/430.1; |
| | <input type="checkbox"/> | <input type="checkbox"/> | US 5318925 A | 19940607 | 4 | Highly abrasion-resistant, flexible | 427/527; | 427/562; |
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| | <input type="checkbox"/> | <input type="checkbox"/> | US 5318923 A | 19940607 | 4 | Highly abrasion-resistant, flexible | 427/226 | 427/126.1; |
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| | <input type="checkbox"/> | <input type="checkbox"/> | US 5318920 A | 19940607 | 4 | processing | 438/50 | 257/E21.266; |
| | <input type="checkbox"/> | <input type="checkbox"/> | US 5318919 A | 19940607 | 4 | Polysilazanes and related | 438/50 | 257/E21.271; |
| | <input type="checkbox"/> | <input type="checkbox"/> | US 5318918 A | 19940607 | 4 | compositions, processes and uses | 438/50 | 257/E21.271; |
| | <input type="checkbox"/> | <input type="checkbox"/> | US 5318917 A | 19940607 | 4 | Method for the surface passivation of | 438/50 | 257/E21.271; |
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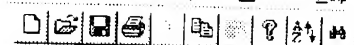
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☒ L7: (70) 6 and (\$20silazane with deposit\$3)

☒ L10: (29) 6 and (\$20silazane with dielectric)

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|----|--------------------------|--------------------------|--------------|------------|-------|------------------------------------------------------------------------------|------------|--------------|
| 40 | <input type="checkbox"/> | <input type="checkbox"/> | US 5318857 A | 19940607 | 8 | Low temperature ozonolysis of silicon and ceramic oxide precursor p | 428/552 | 257/E21.271; |
| 41 | <input type="checkbox"/> | <input type="checkbox"/> | US 5310720 A | 19940510 | 8 | Process for fabricating an integrated circuit device by forming a planarized | 438/760 | 257/E23.118; |
| 42 | <input type="checkbox"/> | <input type="checkbox"/> | US 5262201 A | 19931116 | 8 | Low temperature process for converting silica precursor coatings t | 427/376.2 | 257/E21.243; |
| 43 | <input type="checkbox"/> | <input type="checkbox"/> | US 5183684 A | 19930202 | 11 | Single and multilayer coatings containing aluminum nitride | 427/574 | 257/E21.271; |
| 44 | <input type="checkbox"/> | <input type="checkbox"/> | US 5118530 A | 19920602 | 8 | Use of hydrogen silsesquioxane resin fractions as coating materials | 427/226 | 257/E21.271; |
| 45 | <input type="checkbox"/> | <input type="checkbox"/> | US 5116637 A | 19920526 | 8 | Amine catalysts for the low temperature conversion of silica prec | 427/340 | 257/E21.262; |
| 46 | <input type="checkbox"/> | <input type="checkbox"/> | US 5091162 A | 19920225 | 6 | Perhydrosiloxane copolymers and their use as coating materials | 423/325 | 427/126.1; |
| 47 | <input type="checkbox"/> | <input type="checkbox"/> | US 5063267 A | 19911105 | 8 | Hydrogen silsesquioxane resin fractions and their use as coating mat | 524/284 | 427/126.2; |
| 48 | <input type="checkbox"/> | <input type="checkbox"/> | US 5055431 A | 19911008 | 14 | Polysilazanes and related compositions, processes and uses | 501/96.2 | 502/232; |
| 49 | <input type="checkbox"/> | <input type="checkbox"/> | US 5008422 A | 19910416 | 29 | Polysilazanes and related compositions, processes and uses | 556/412 | 257/E21.262; |
| 50 | <input type="checkbox"/> | <input type="checkbox"/> | US 5008320 A | 19910416 | 10 | Platinum or rhodium catalyzed multilayer ceramic coatings from hydr | 524/361 | 423/324; |
| 51 | <input type="checkbox"/> | <input type="checkbox"/> | US 4997482 A | 19910305 | 9 | Coating composition containing hydrolyzed silicate esters and other m | 106/287.16 | 264/624; |
| 52 | <input type="checkbox"/> | <input type="checkbox"/> | US 4952715 A | 19900828 | 15 | Polysilazanes and related compositions, processes and uses | 556/409 | 423/353; |
| 53 | <input type="checkbox"/> | <input type="checkbox"/> | US 4950050 A | 19900821 | 16 | Electroluminescent device with | 312/504 | 556/402; |

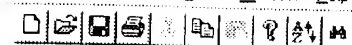


☒ L7: (70) 6 and (\$20silazane with deposit\$3)
☒ L10: (29) 6 and (\$20silazane with dielectric)

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| 54 | <input type="checkbox"/> | <input type="checkbox"/> | US 4911992 A | 19900327 | 18 | Platinum or rhodium catalyzed multilayer ceramic coatings from hydr | 428/698 | 428/690; |
| 55 | <input type="checkbox"/> | <input type="checkbox"/> | US 4898907 A | 19900206 | 8 | Compositions of platinum and rhodium catalyst in combination with | 524/490 | 427/122; |
| 56 | <input type="checkbox"/> | <input type="checkbox"/> | US 4863755 A | 19890905 | 24 | Plasma enhanced chemical vapor deposition of thin films of silicon nitri | 427/574 | 427/126.2; |
| 57 | <input type="checkbox"/> | <input type="checkbox"/> | US 4822697 A | 19890418 | 13 | Platinum and rhodium catalysis of low temperature formation multilayer | 428/698 | 106/287.1; |
| 58 | <input type="checkbox"/> | <input type="checkbox"/> | US 4808653 A | 19890228 | 8 | Coating composition containing hydrogen silsesquioxane resin and ot | 524/398 | 106/287.14; |
| 59 | <input type="checkbox"/> | <input type="checkbox"/> | US 4756977 A | 19880712 | 13 | Multilayer ceramics from hydrogen silsesquioxane | 428/704 | 257/E21.293; |
| 60 | <input type="checkbox"/> | <input type="checkbox"/> | US 4753856 A | 19880628 | 15 | Multilayer ceramic coatings from silicate esters and metal oxides | 428/698 | 427/579; |
| 61 | <input type="checkbox"/> | <input type="checkbox"/> | US 4753855 A | 19880628 | 14 | Multilayer ceramic coatings from metal oxides for protection of electro | 428/702 | 257/E21.262; |
| 62 | <input type="checkbox"/> | <input type="checkbox"/> | US 4751191 A | 19880614 | 8 | Method of fabricating solar cells with silicon nitride coating | 438/72 | 257/E21.271; |
| 63 | <input type="checkbox"/> | <input type="checkbox"/> | US 4749631 A | 19880607 | 17 | Multilayer ceramics from silicate esters | 428/704 | 106/287.14; |
| 64 | <input type="checkbox"/> | <input type="checkbox"/> | US 4719125 A | 19880112 | 6 | Cyclosilazane polymers as dielectric films in integrated circuit fabrication t | 438/780 | 257/E21.266; |

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☒ L7: (70) 6 and (\$20silazane with deposit\$3)
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| 65 | <input type="checkbox"/> | <input type="checkbox"/> | US 4599243 A | 19860708 | 11 | metal oxides for protection of electro | 438/72 | 257/E23.118; |
| 66 | <input type="checkbox"/> | <input type="checkbox"/> | US 4562091 A | 19851231 | 9 | Method of fabricating solar cells with | 438/72 | 136/256; |
| 67 | <input type="checkbox"/> | <input type="checkbox"/> | US 4493855 A | 19850115 | 10 | silicon nitride coating | 428/704 | 136/258; |
| 68 | <input type="checkbox"/> | <input type="checkbox"/> | US 4451969 A | 19840605 | 9 | Multilayer ceramics from silicate | 428/704 | 136/256; |
| 69 | <input type="checkbox"/> | <input type="checkbox"/> | WO 200217374 A | 20020228 | 60 | esters | 438/780 | 257/E21.271; |
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| | | | | | | films in integrated circuit fabrication t | 216/18 | 257/E21.271; |
| | | | | | | Use of plasma polymerized | 427/489 | 216/40; |
| | | | | | | organosilicon films in fabrication of li | 427/489 | 427/489; |
| | | | | | | Use of plasma polymerized | 438/670 | 204/165; |
| | | | | | | orgaosilicon films in fabrication of lift | 438/62 | 427/488; |
| | | | | | | Use of plasma polymerized | | 204/192.32; |
| | | | | | | organosilicon films in fabrication of li | | 427/489; |
| | | | | | | Method of fabricating solar cells | | 136/256; |
| | | | | | | Formation of silicon nitride film for | | 257/E21.174; |
| | | | | | | semiconductor device, involves suppl | | |
| | | | | | | Plasma-deposited abrasion-resistant | | |
| | | | | | | coating prodn. - using as plasma mon | | |